PTO/SB/06A(10-01)
Approved for use through 10/31/2002, OAG 651-0031
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commission unless it contains a valid OMB control number.

Under the Peperwork Reduction Act of 1995, no persons are required to res Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE 10/789,044 **Application Number** STATEMENT BY APPLICANT
(Use as many sheets as necessary) February 27, 2004 **Filing Date First Named Inventor** Ahn, Kie **Group Art Unit** 2891 **Examiner Name** Menz, Douglas Attorney Docket No: 1303.070US2 Sheet 1 of 2

		US PATE	NT DOCUMENTS	
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
M	US-2003/0043637-A1	03/06/2003	Forbes, Leonard, et al.	08/30/2001
D/	US-2004/0159863-A1	08/19/2004	Eldridge, Jerome M., et al.	02/18/2004
MM	US-2005/0023574-A1	02/03/2005	Forbes, L., et al.	09/02/2004
Vm.	US-2005/0023595-A1	02/03/2005	Forbes, L., et al.	08/31/2004
DM	US-2005/0023602-A1	02/03/2005	Forbes, L., et al.	08/30/2004
_V/M	US-2005/0023603-A1	02/03/2005	Eldridge, J. M., et al.	08/30/2004
pm	US-2005/0026349-A1	02/03/2005	Forbes, L., et al.	09/01/2004
DM	US-2005/0030825-A1	02/10/2005	Ahn, K. Y.	08/31/2004
bm	US-2005/0032342-A1	02/10/2005	Forbes, L., et al.	08/30/2004
DM	US-2005/0077519-A1	04/14/2005	Ahn, Kie, et al.	10/10/2003
DM	US-2005/0124174-A1	06/09/2005	Ahn, K. Y., et al.	01/07/2005
DM	US-2005/0138262-A1	06/23/2005	Forbes, Leonard	12/18/2003
_WN	US-2005/0145957-A1	07/07/2005	Ahn, K. Y., et al.	02/16/2005
BM	US-2005/0158973-A1	07/21/2005	Ahn, K. Y., et al.	01/14/2005
PM	US-2005/0164521-A1	07/28/2005	Ahn, Kie Y., et al.	03/21/2005
ON	US-5,562,952	10/08/1996	Nakahigashi, Takahiro , et al.	04/04/1995
DM	US-5,674,563	10/07/1997	Tarui, Yasuo , et al.	09/14/1994
DM	US-5,827,571	10/27/1998	Lee, Seaung S., et al.	09/17/1997
DM	US-6,025,225	02/15/2000	Forbes, Leonard, et al.	01/22/1998
DM	US-6,454,912	09/24/2002	Ahn, Kie Y., et al.	03/15/2001
W M	US-6,509,280	01/21/2003	Choi, Sung-Je	02/13/2002
pm	US-6,541,079	04/01/2003	Bojarczuk, Jr., N. A., et al.	10/25/1999
M	US-6,778,441	08/17/2004	Forbes, L., et al.	08/30/2001
M	US-6,787,370	09/07/2004	Forbes, Leonard	12/16/2002
m	US-6,858,120	02/22/2005	Ahn, Kie , et al.	08/09/2002
DW.	US-6,858,444	02/22/2005	Ahn, K. Y., et al.	06/20/2003
MM	US-6,884,739	04/26/2005	Ahn, K. Y., et al.	08/15/2002
m	US-6,893,984	05/17/2005	Ahn, K. Y., et al.	02/20/2002
pM	US-6,900,122	05/31/2005	Ahn, K. Y., et al.	12/20/2001
DM	US-6,914,800	07/05/2005	Ahn, K. Y., et al.	08/31/2004
Dh.	US-6,921,702	07/26/2005	Ahn, K. Y., et al.	07/30/2002
DM	US-6,930,346	08/16/2005	Ahn, K. Y., et al.	08/31/2004

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	T²	

	-		 	1 1
EXAMINER		2	DATE CONSIDERED	10/28/05
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PTO/SB/08A(10-01)
Approved for use through 10/31/2002, OMB 651-0031
and & Trademark Office: U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449A/PTO INFORMATION DISCLOSURE	Complete if Known			
STATEMENT BY APPLICANT	Application Number	10/789,044		
(Use as many sheets as necessary)	Filing Date	February 27, 2004		
	First Named Inventor	Ahn, Kie		
	Group Art Unit	2891		
	Examiner Name	Menz, Douglas		
Sheet 2 of 2	Attorney Docket No: 1303.070US2			

	OTHE	R DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T'
VM		AHN, KIE Y., et al., "ALD OF AMORPHOUS LANTHANIDE DOPED TIOX FILMS", U.S. Application Serial No. 11/092,072; filed March 29, 2005	
DM		AHN, KIE Y., et al., "ATOMIC LAYER DEPOSITED HAFNIUM TANTALUM OXIDE DIELECTRICS", U.S. Application Serial No. 11/029,757; filed January 5, 2005	
1m		AHN, KIE Y., et al., "ATOMIC LAYER DEPOSITED LANTHANUM ALUMINUM OXIDE DIELECTRIC LAYER", U.S. Application Serial No. 10/930,167; filed August 31, 2004	
ym		AHN, KIE Y., et al., "ATOMIC LAYER DEPOSITED LANTHANUM HAFNIUM OXIDE DIELECTRICS", U.S. Application Serial No. 11/010,529; filed December 13, 2004	
on		AHN, KIE Y., et al., "ATOMIC LAYER DEPOSITED TITANIUM ALUMINUM OXIDE FILMS", U.S. Application Serial No. 10/931,533; filed August 31, 2004	
0m		AHN, KIE Y., et al., "ATOMIC LAYER DEPOSITION OF Hf3N4/Hf02 FILMS AS GATE DIELECTRICS", U.S. Application Serial No. 11/063,717; filed February 23, 2005	
VM		AHN, KIE Y., et al., "ATOMIC LAYER DEPOSITION OF ZIRCONIUM-DOPED TANTALUM OXIDE FILMS", <u>U.S. Application Serial No. 10/909,959; filed August 2, 2004</u>	
0M		AHN, KIE Y., et al., "ATOMIC LAYER DEPOSITION OF Zr3N4/ZrO2 FILMS AS GATE DIELECTRICS", U.S. Application Serial No. 11/058,563; filed February 15, 2005	
M		AHN, KIE Y., et al., "HYBRID ALD-CVD OF PrXOY/ZrO2 FILMS AS GATE DIELECTRICS", U.S. Application Serial No. 11/010,766; filed December 13, 2004	
VM		AHN, KIE Y., et al., "RUTHENIUM GATE FOR A LANTHANIDE OXIDE DIELECTRIC LAYER", U.S. Application Serial No. 10/926,812; filed August 26, 2004	

EXAMINER DATE CONSIDERED 10/28/07